

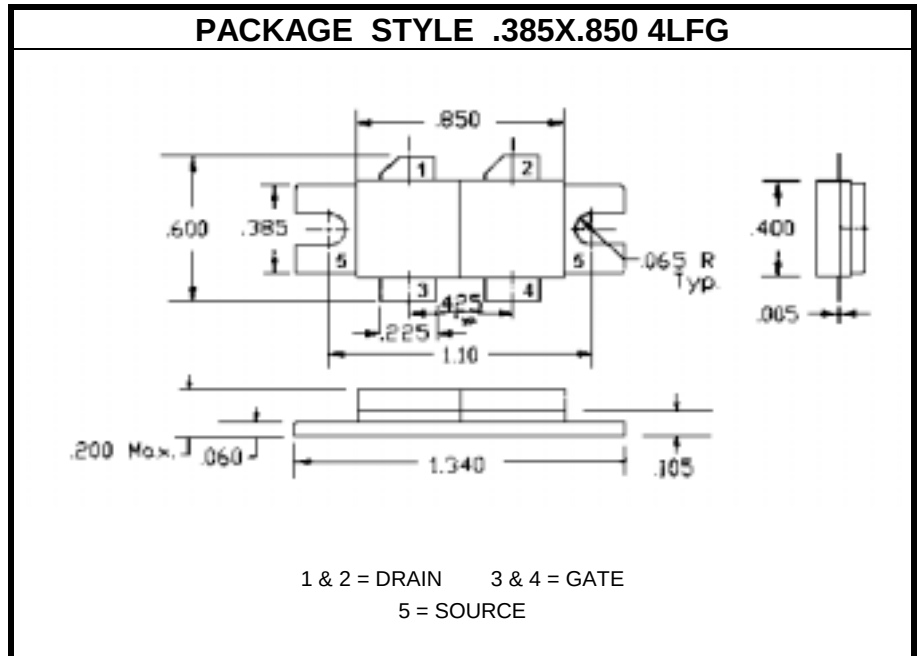
RF POWER VDMOS TRANSISTOR

DESCRIPTION:

The **ASI BLF368** is a Dual Common Source N-Channel Enhancement-Mode VDMOS. designed for RF Applications.

MAXIMUM RATINGS

I_D	27 A
V_{DSS}	70 V
V_{GS}	± 20 V
P_{DISS}	465 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.35°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	$I_{DS} = 120\text{ mA}$ $V_{GS} = 0\text{ V}$	65			V
I_{DSS}	$V_{DS} = 28\text{ V}$ $V_{GS} = 0\text{ V}$			6.0	mA
I_{GSS}	$V_{DS} = 0\text{ V}$ $V_{GS} = 30\text{ V}$			1.0	μA
V_{GS}	$I_{DS} = 600\text{ mA}$ $V_{GS} = V_{DS}$	1.0		7.0	V
gM	$V_{DS} = 10\text{ V}$ $V_{GS} = 5.0\text{ V}$		7.2		mho
$R_{DS(on)}$	$V_{GS} = 20\text{ V}$ $I_{DS} = 15\text{ A}$	5.0			Ω
I_{DSAT}	$V_{GS} = 20\text{ V}$ $V_{DS} = 10\text{ V}$		42		A
C_{iss} C_{oss} C_{rss}	$V_{DS} = 28\text{ V}$ $V_{GS} = 0\text{ V}$ $f = 1.0\text{ MHz}$		300 192 18		pF
G_{ps} η ψ	$V_{DS} = 28\text{ V}$ $I_{DQ} = 1.2\text{ A}$ $P_{out} = 300\text{ W}$ $f = 175\text{ MHz}$	13	55	20:1	dB % Relative